ABSTRACT

Insulating films 21 through 24 of CF films (fluorine-contained carbon films) are formed on a substrate (not shown). In addition, Cu wiring layers 25 and 26 are formed on the CF films 21 and 23 via an adhesion layer 29 which comprises a Ti layer and a TiC layer. By forming the insulating films 21 through 24 of CF films, Cu in the wiring layers is prevented from diffusing into the insulating films 21 through 24. The relative dielectric constant of the CF film is smaller than the relative dielectric constant of a BCB film.